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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SDIO, QSPI, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f413rgt6tr

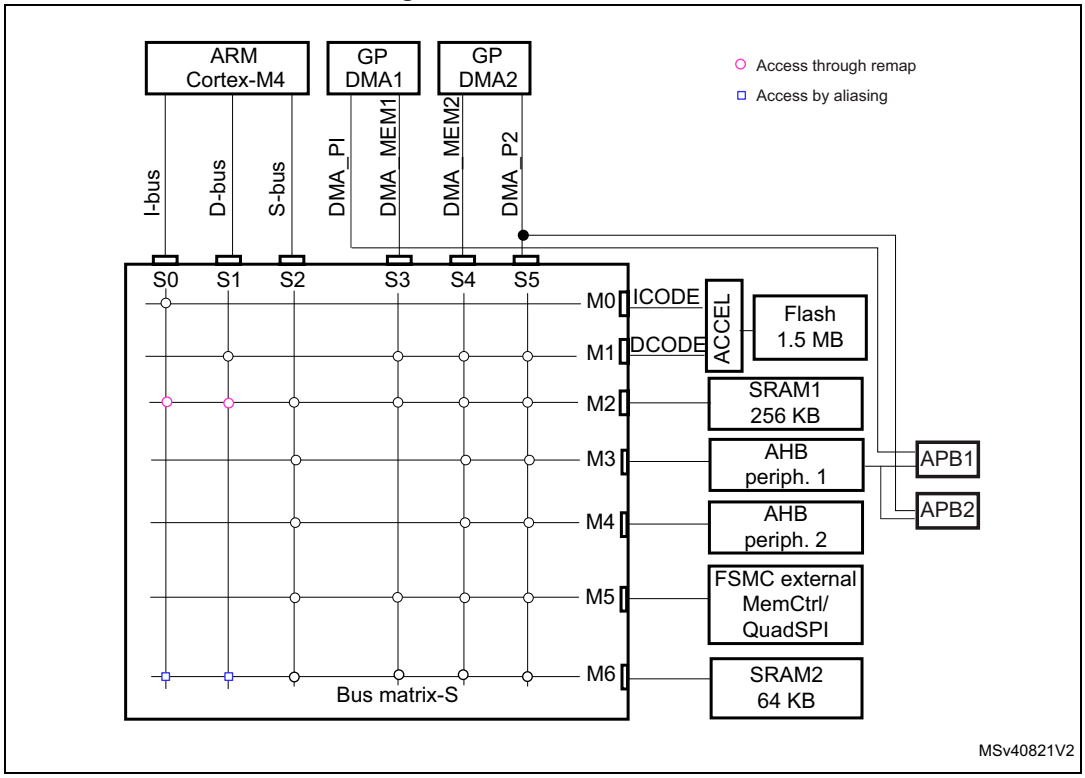
3.7 Embedded SRAM

All devices embed 320 Kbytes of system SRAM which can be accessed (read/write) at CPU clock speed with 0 wait states.

3.8 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs) and the slaves (Flash memory, RAM, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 5. Multi-AHB matrix



CPU can access SRAM1 memory via S-bus, when SRAM1 is mapped at the address range: 0x2000 0000 to 0x2003 FFFF.

CPU can access SRAM2 memory via S-bus, when SRAM2 is mapped at the address range: 0x2004 0000 to 0x2004 FFFF.

CPU can access SRAM1 memory via I-bus and D-bus, when SRAM1 is remapped at address 0x0000 0000 either by booting from RAM memory or by the remap mode.

CPU can access SRAM2 memory via I-bus and D-bus, when SRAM2 is mapped at the address range: 0x1000 0000 to 0x1000 FFFF.

Performance boosts up, when the CPU access SRAM memory via the I-bus.

buses and high-speed APB domains is 100 MHz. The maximum allowed frequency of the low-speed APB domain is 50 MHz.

The devices embed a dedicated PLL (PLLI2S) which allows to achieve audio class performance. In this case, the I^2S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

3.15 Boot modes

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash memory
- Boot from system memory
- Boot from embedded SRAM

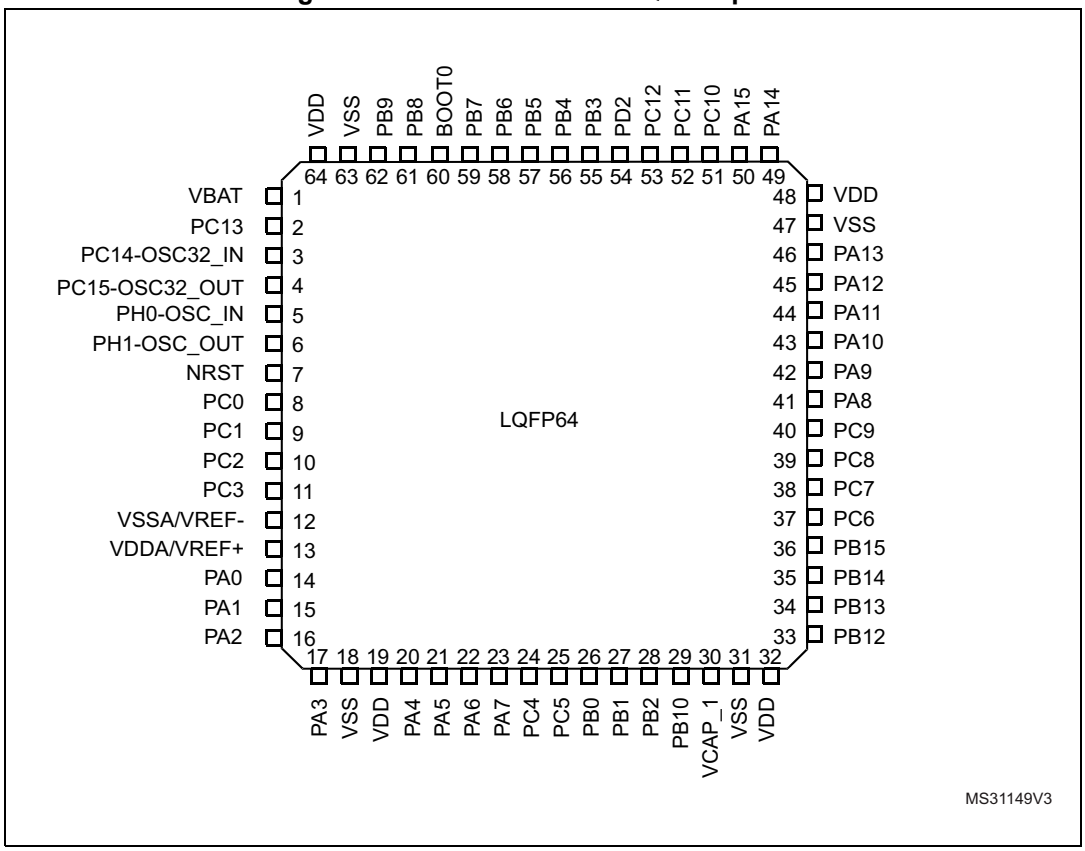
The boot loader is located in system memory. It is used to reprogram the Flash memory by using one of the interface listed in the *Table 3* or the USB OTG FS in device mode through DFU (device firmware upgrade).

Table 3. Embedded bootloader interfaces

Package	USART1 PA9/ PA10	USART2 PD6/ PD5	USART3 PB11/ PB10	I2C1 PB6/ PB7	I2C2 PF0/ PF1	I2C3 PA8/ PB4	I2C FMP1 PB14/ PB15	SPI1 PA4/ PA5/ PA6/ PA7	SPI3 PA15/ PC10/ PC11/ PC12	SPI4 PE11/ PE12/ PE13/ PE14	CAN2 PB5/ PB13	USB PA11 /P12
UFQFPN48	Y	-	-	Y	-	Y	Y	Y	-	-	Y	Y
LQFP64	Y	-	-	Y	-	Y	Y	Y	Y	-	Y	Y
WLCSP81	Y	-	-	Y	-	Y	Y	Y	Y	Y	Y	Y
LQFP100	Y	Y	-	Y	-	Y	Y	Y	Y	Y	Y	Y
LQFP144	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y
UFBGA100	Y	Y	Y	Y	-	Y	Y	Y	Y	Y	Y	Y
UFBGA144	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y

For more detailed information on the bootloader, refer to Application Note: AN2606, *STM32™ microcontroller system memory boot mode*.

Figure 13. STM32F413xG/H LQFP64 pinout



1. The above figure shows the package top view.

Table 10. STM32F413xG/H pin definition (continued)

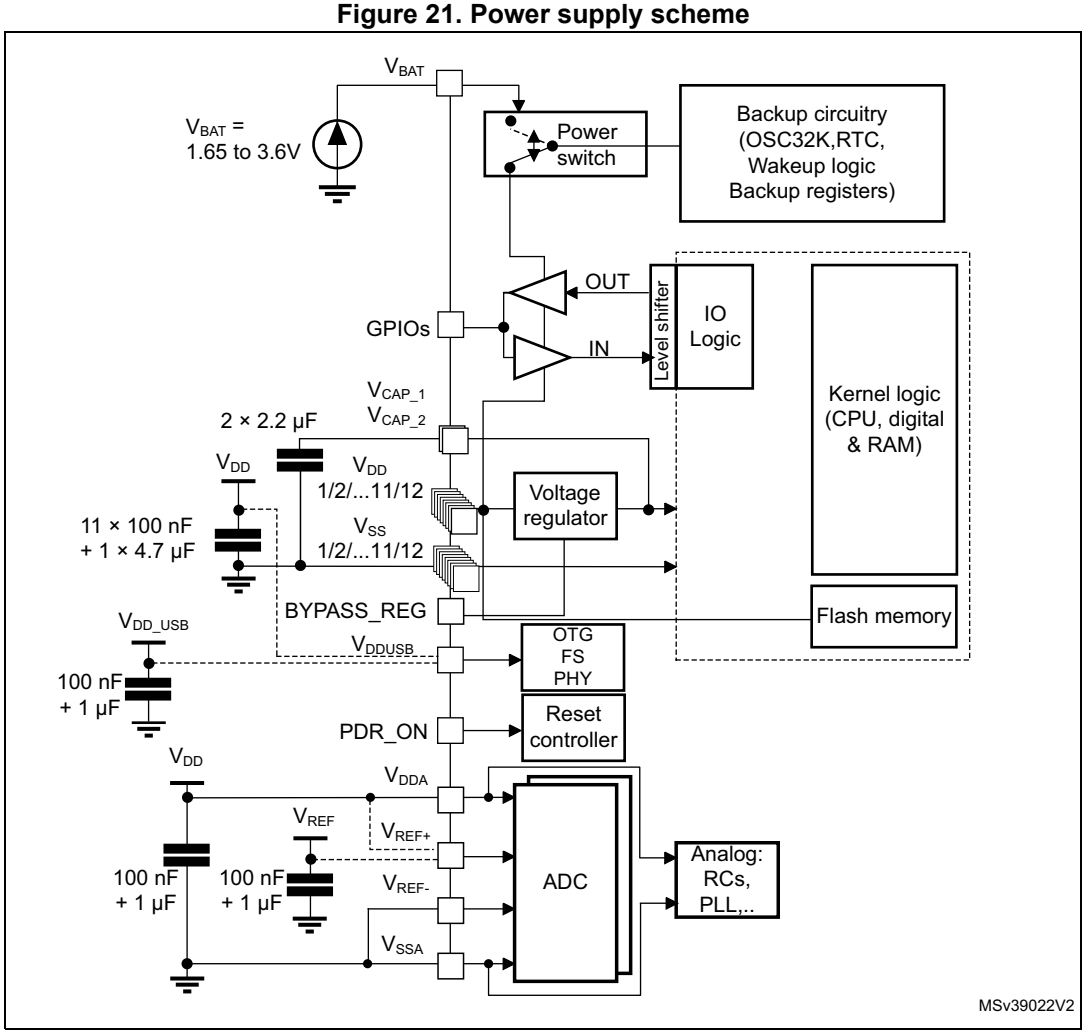
Pin Number							Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP81	LQFP100	UFBGA100	UFBGA144	LQFP144						
-	-	NC	62	H10	K12	86	PD15	I/O	FTf	(2)	TIM4_CH4, I2CFMP1_SDA, DFSDM2_DATIN0, UART9_TX, FSMC_D1/FSMC_DA1, EVENTOUT	-
-	-	-	-	-	J12	87	PG2	I/O	FT	-	FSMC_A12, EVENTOUT	-
-	-	-	-	-	J11	88	PG3	I/O	FT	-	FSMC_A13, EVENTOUT	-
-	-	-	-	-	J10	89	PG4	I/O	FT	-	FSMC_A14, EVENTOUT	-
-	-	-	-	-	H12	90	PG5	I/O	FT	-	FSMC_A15, EVENTOUT	-
-	-	-	-	-	H11	91	PG6	I/O	FT	-	QUADSPI_BK1_NCS, EVENTOUT	-
-	-	-	-	-	H10	92	PG7	I/O	FT	-	USART6_CK, EVENTOUT	-
-	-	-	-	-	G11	93	PG8	I/O	FT	-	USART6_RTS, EVENTOUT	-
-	-	-	-	-	-	94	VSS	S	-	-	-	-
-	-	-	-	-	F10	-	VDD	S	-	-	-	-
-	-	F1	-	-	C11	95	VDDUSB	S	-	-	-	-
-	37	D5	63	E12	G12	96	PC6	I/O	FTf	-	TIM3_CH1, TIM8_CH1, I2CFMP1_SCL, I2S2_MCK, DFSDM1_CKIN3, DFSDM2_DATIN6, USART6_TX, FSMC_D1/FSMC_DA1, SDIO_D6, EVENTOUT	-
-	38	D4	64	E11	F12	97	PC7	I/O	FTf	-	TIM3_CH2, TIM8_CH2, I2CFMP1_SDA, SPI2_SCK/I2S2_CK, I2S3_MCK, DFSDM2_CKIN6, USART6_RX, DFSDM1_DATIN3, SDIO_D7, EVENTOUT	-

Table 13. STM32F413xG/H register boundary addresses (continued)

Bus	Boundary address	Peripheral
APB2	0x4001 6800- 0x4001 FFFF	Reserved
	0x4001 6400 - 0x4001 67FF	DFSDM2
	0x4001 6000 - 0x4001 63FF	DFSDM1
	0x4001 5C00 - 0x4001 5FFF	Reserved
	0x4001 5800 - 0x4001 5BFF	SAI1
	0x4001 5400 - 0x4001 57FF	Reserved
	0x4001 5000 - 0x4001 53FF	SPI5/I2S5
	0x4001 4C00 - 0x4001 4FFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4/I2S4
	0x4001 3000 - 0x4001 33FF	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1/2/3
	0x4001 1C00 - 0x4001 1FFF	UART10
	0x4001 1800 - 0x4001 1BFF	UART9
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1

6.1.6 Power supply scheme

Figure 21. Power supply scheme



1. To connect PDR_ON pin, refer to Section: Power supply supervisor.
2. The 4.7 µF ceramic capacitor must be connected to one of the V_{DD} pin.
3. VCAP_2 pad is only available on 100-pin and 144-pin packages.
4. V_{DDA}=V_{DD} and V_{SSA}=V_{SS}.
5. V_{DDUSB} is a dedicated independent USB power supply for the on-chip full-speed OTG PHY module and associated DP/DM GPIOs. V_{DDUSB} value does not depend on the V_{DD} and V_{DDA} values, but it must be the last supply to be provided and the first to disappear.

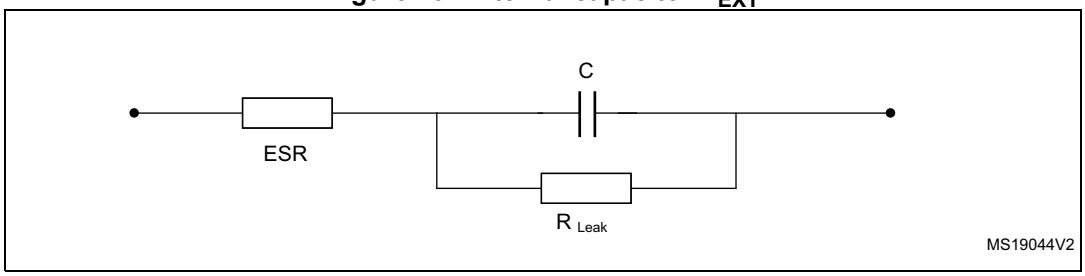
Caution: Each power supply pair (for example V_{DD}/V_{SS}, V_{DDA}/V_{SSA}) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure good operation of the device. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect operation of the device.

6.3.2 VCAP_1/VCAP_2 external capacitors

Stabilization for the main regulator is achieved by connecting the external capacitor C_{EXT} to the VCAP_1 and VCAP_2 pins. For packages supporting only 1 VCAP pin, the 2 CEXT capacitors are replaced by a single capacitor.

C_{EXT} is specified in *Table 19*.

Figure 23. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 19. VCAP_1/VCAP_2 operating conditions(1)

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor with the pins VCAP_1 and VCAP_2 available	2.2 µF
ESR	ESR of external capacitor with the pins VCAP_1 and VCAP_2 available	< 2 Ω
CEXT	Capacitance of external capacitor with a single VCAP pin available	4.7 µF
ESR	ESR of external capacitor with a single VCAP pin available	< 1 Ω

1. When bypassing the voltage regulator, the two 2.2 µF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up/power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 20. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

Table 24. Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
				T_A= 25 °C	T_A= 25 °C	T_A= 85 °C	T_A= 105 °C	T_A= 125 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON, all peripherals enabled(2)	100	33.3	35.32(3)	35.65	37.65	41.26(3)	mA
			84	26.8	28.45(3)	28.97	30.82	34.39(3)	
			64	18.6	19.74(3)	20.35	22.11	25.35(3)	
			50	14.6	15.57	16.41	18.21	21.46	
			25	7.8	8.37	9.64	11.32	14.68	
			20	6.7	7.25	8.40	10.25	13.45	
		HSI, PLL OFF(4), all peripherals enabled(2)	16	4.6	4.96	6.39	8.20	11.54	
			1	0.8	0.86	2.51	4.34	7.65	
		External clock, PLL ON, all peripherals disabled(2)	100	15.7	16.74(3)	17.62	19.50	23.16(3)	
			84	12.7	13.57(3)	14.60	16.38	19.98(3)	
			64	9.0	9.62(3)	10.60	12.37	15.58(3)	
			50	7.1	7.69	8.79	10.63	13.79	
			25	4.0	4.52	5.68	7.44	10.68	
			20	3.4	4.03	5.23	6.90	10.27	
		HSI, PLL OFF, all peripherals disabled(2)	16	2.3	2.44	4.00	5.81	9.13	
			1	0.6	0.70	2.35	4.18	7.49	

1. Guaranteed by characterization results.
2. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.
3. Tested in production
4. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered

Figure 24. Typical V_{BAT} current consumption (LSE and RTC ON/LSE oscillator "low power" mode selection)

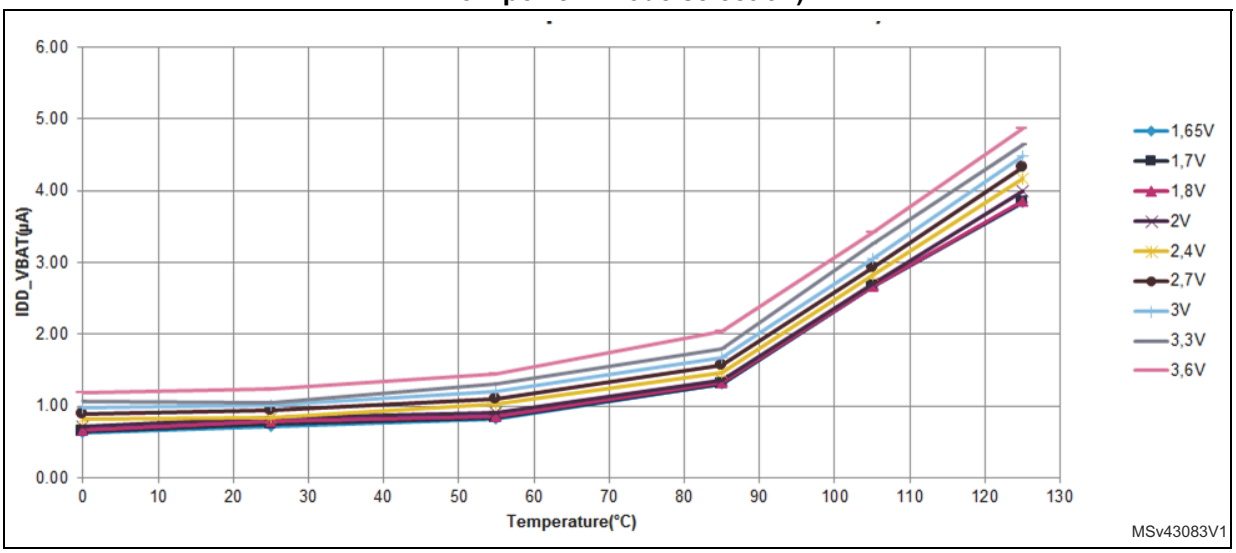


Figure 25. Typical V_{BAT} current consumption (LSE and RTC ON/LSE oscillator "high drive" mode selection)

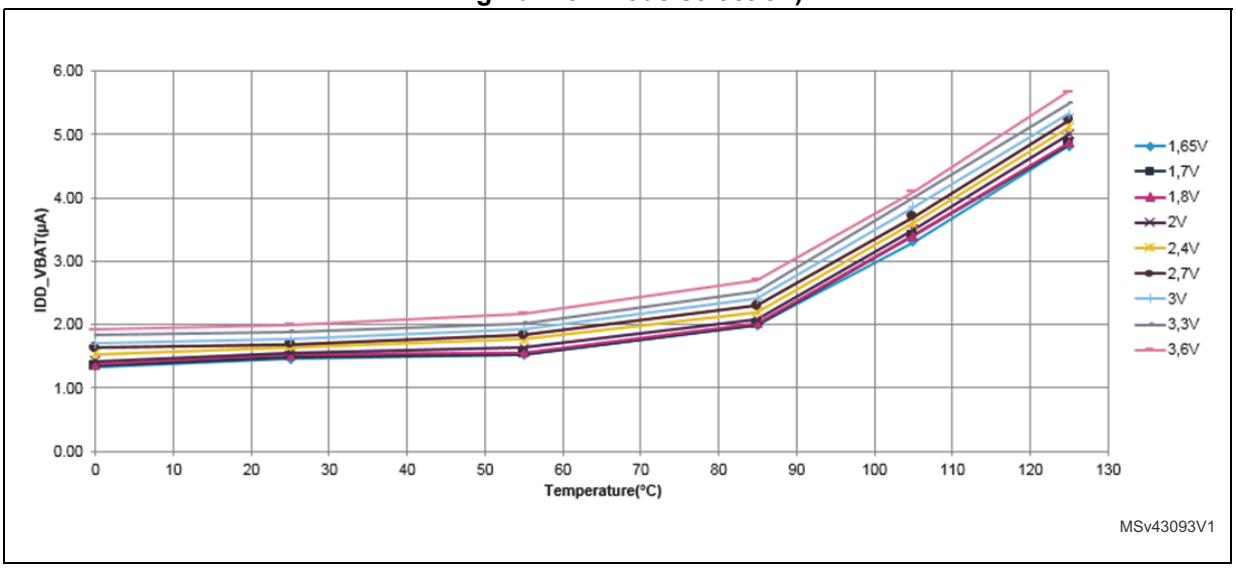


Table 39. Peripheral current consumption (continued)

Peripheral		I_{DD} (Typ)			Unit
		Scale 1	Scale 2	Scale 3	
APB1	AHB-APB1 bridge	0.90	0.88	0.81	µA/MHz
	TIM2	13.08	12.48	11.16	
	TIM3	9.98	9.50	8.50	
	TIM4	9.88	9.43	8.44	
	TIM5	13.14	12.52	11.19	
	TIM6	1.94	1.86	1.66	
	TIM7	1.86	1.79	1.56	
	TIM12	5.56	5.29	4.72	
	TIM13	3.44	3.29	2.94	
	TIM14	3.66	3.48	3.09	
	LPTIM1	7.34	7.00	6.25	
	WWDG	0.64	0.62	0.53	
	SPI2/I2S2	3.02	2.88	2.56	
	SPI3/I2S3	3.06	2.90	2.59	
	USART2	3.30	3.14	2.81	
	USART3	3.32	3.14	2.81	
	UART4	3.18	3.02	2.69	
	UART5	3.26	3.10	2.75	
	I2C1	3.20	3.05	2.72	
	I2C2	3.30	3.14	2.81	
	I2C3	3.26	3.10	2.78	
	I2CFMP1	5.22	4.98	4.44	
	CAN1	5.58	5.31	4.75	
	CAN2	5.14	4.88	4.38	
	CAN3	5.70	5.43	4.84	
	PWR	0.90	0.86	0.75	
	DAC1	2.14	2.05	1.81	
	UART7	3.08	2.93	2.59	
	UART8	3.10	2.95	2.63	

Low-speed internal (LSI) RC oscillator

Table 46. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI} (2)	Frequency	16.1	32.0	47.0	kHz
$t_{su(LSI)}$ (3)	LSI oscillator startup time	-	15.0	40.0	µs
$I_{DD(LSI)}$ (3)	LSI oscillator power consumption	-	0.4	0.6	µA

1. V_{DD} = 3 V, T_A = –40 to 125 °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Figure 32. ACC_{LSI} versus temperature

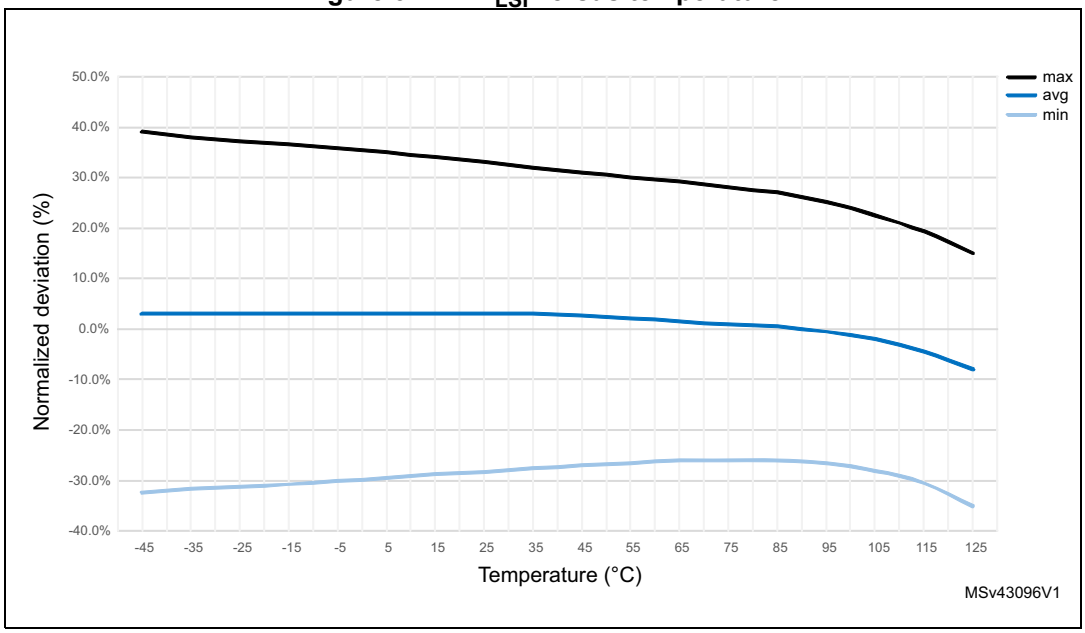


Table 48. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock(1)	-		0.95(2)	1	2.10	MHz
$f_{PLLI2SQ\_OUT}$	48 MHz PLLI2SQ multiplier output clock	-		-	48	75	
$f_{PLLI2SR\_OUT}$	PLLI2SR multiplier output clock for I2S and SAI	-		-	-	216	
f_{VCO_OUT}	PLLI2S VCO output	-		100	-	432	
t_{LOCK}	PLLI2S lock time	VCO freq = 100 MHz		75	-	200	µs
		VCO freq = 432 MHz		100	-	300	
Jitter(3)	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48 kHz period, N=432, R=5	RMS	-	90	-	ps
			peak to peak	-	±280	-	
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples		-	90	-	
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples		-	400	-	
$I_{DD(PLLI2S)}$(4)	PLLI2S power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLI2S)}$(4)	PLLI2S power consumption on V_{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

2. The USB OTG FS functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design.
4. R_L is the load connected on the USB OTG FS drivers.

Note: When VBUS sensing feature is enabled, PA9 should be left at their default state (floating input), not as alternate function. A typical 200 µA current consumption of the embedded sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 when the feature is enabled.

Figure 47. USB OTG FS timings: definition of data signal rise and fall time

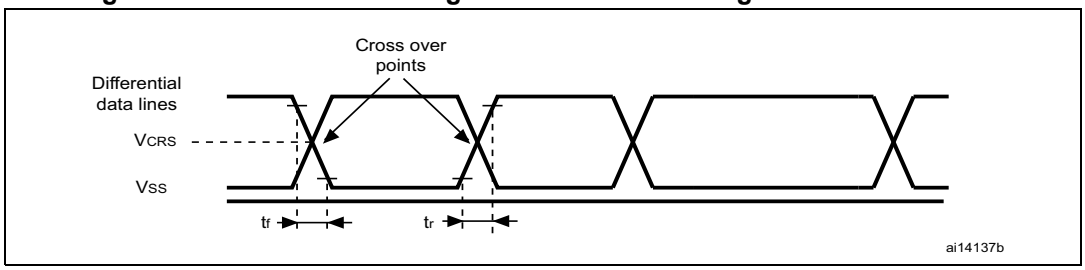


Table 74. USB OTG FS electrical characteristics(1)

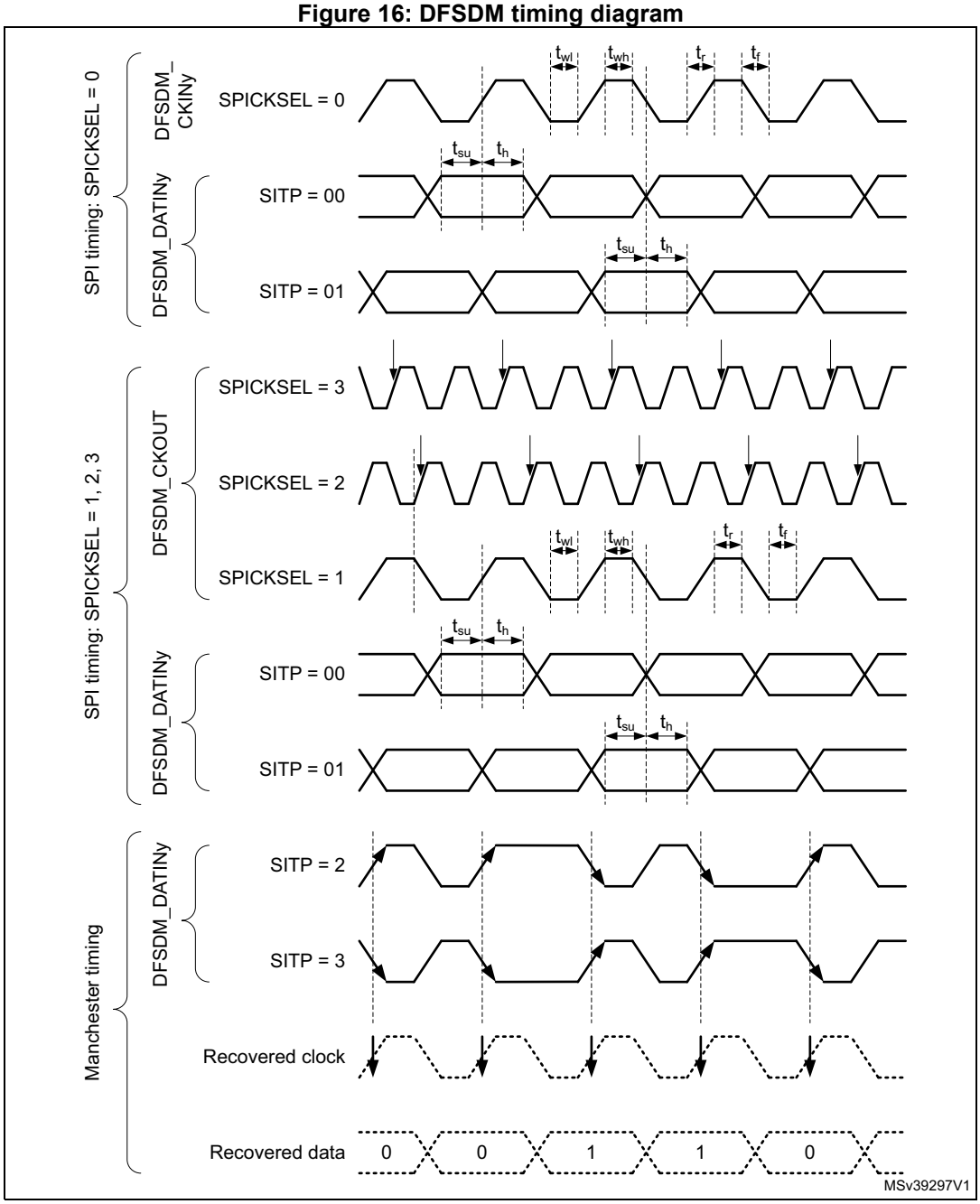
Driver characteristics					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification - Chapter 7 (version 2.0).

CAN (controller area network) interface

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (CANx_TX and CANx_RX).

Figure 16: DFSDM timing diagram

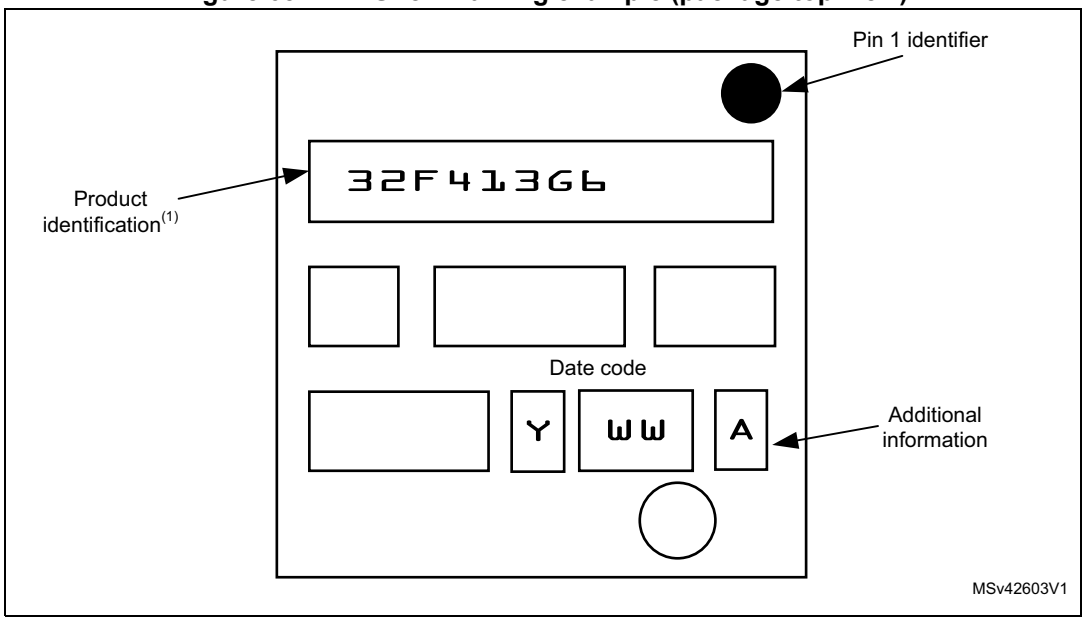


Device marking for WLCSP81

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 65. WLCSP81 marking example (package top view)



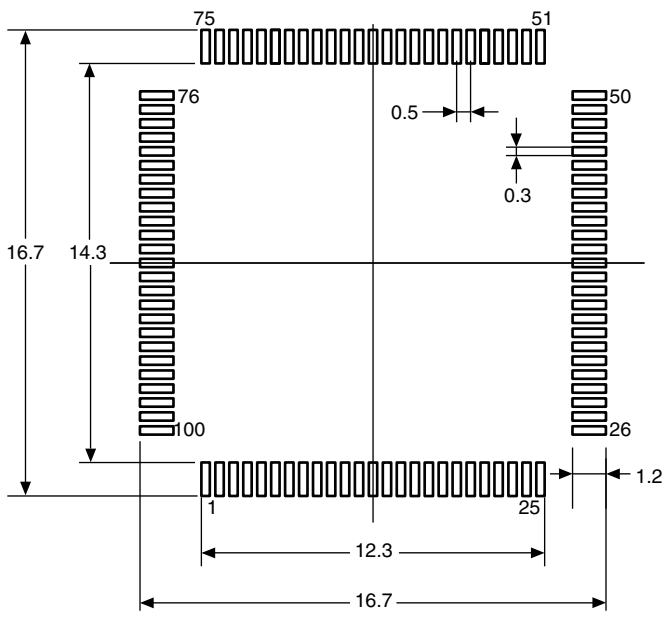
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 107. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

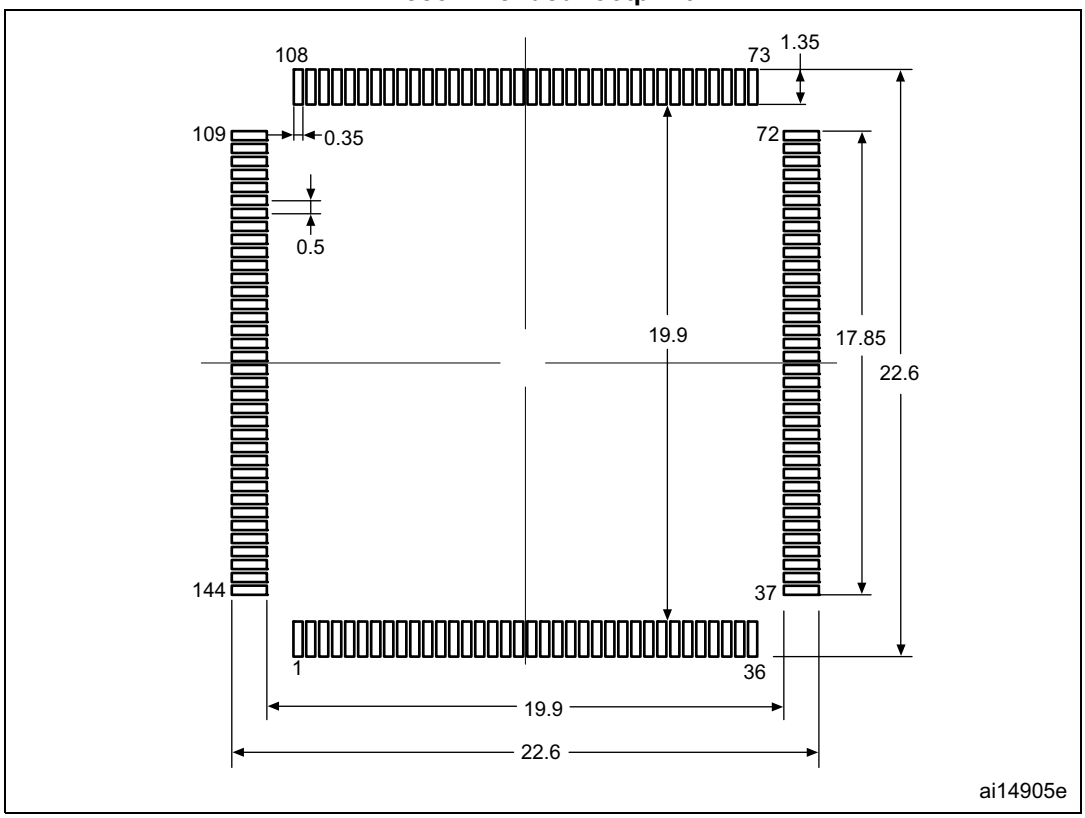
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 73. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are in millimeters.

Figure 76. LQFP144 - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Table 111. UFBGA144 - 144-ball, 10 x 10 mm, 0.80 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
F	0.550	0.600	0.650	0.0177	0.0197	0.0217
ddd	-	-	0.080	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 82. UFBGA144 - 144-pin, 10 x 10 mm, 0.80 mm pitch, ultra fine pitch ball grid array recommended footprint

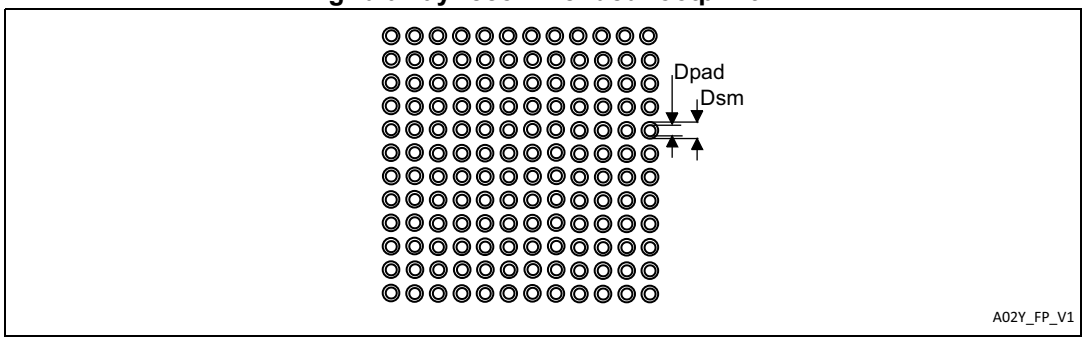


Table 112. UFBGA144 recommended PCB design rules (0.80 mm pitch BGA)

Dimension	Recommended values
Pitch	0.80 mm
Dpad	0.400 mm
Dsm	0.550 mm typ. (depends on the soldermask registration tolerance)

Note: Non solder mask defined (NSMD) pads are recommended.

4 to 6 mils solder paste screen printing process.

Stencil opening is 0.400 mm.

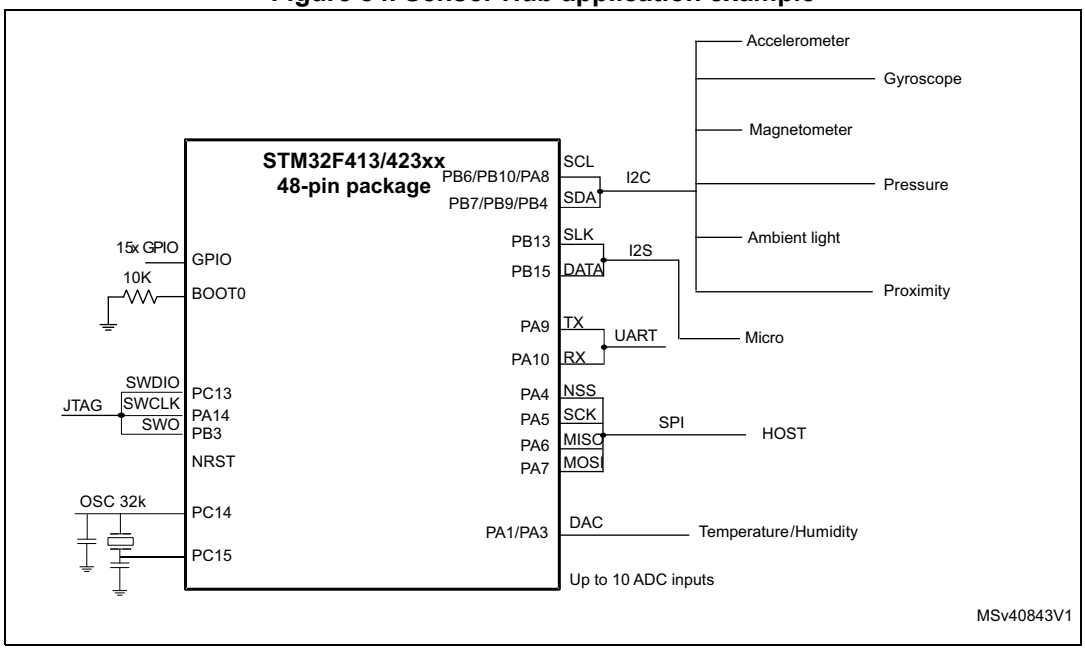
Stencil thickness is between 0.100 mm and 0.125 mm.

Pad trace width is 0.120 mm.

Appendix B Application block diagrams

B.1 Sensor Hub application example

Figure 84. Sensor Hub application example



Revision history

Table 115. Document revision history

Date	Revision	Changes
29-Aug-2016	1	Initial release.
21-Oct-2016	2	Updated: – *Table 10: STM32F413xG/H pin definition* – *Section 7: Package information* – *Figure 65: WLCSP81 marking example (package top view)*
13-Dec-2016	3	Updated: – *Table 39: Peripheral current consumption* – *Table 55: EMI characteristics for LQFP144* – *Table 56: ESD absolute maximum ratings* – *Table 70: QSPI dynamic characteristics in SDR mode* – *Table 111: UFBGA144 - 144-ball, 10 x 10 mm, 0.80 mm pitch, ultra fine pitch ball grid array package mechanical data* – *Figure 81: UFBGA144 - 144-pin, 10 x 10 mm, 0.80 mm pitch, ultra fine pitch ball grid array package outline*
09-Mar-2017	4	Updated: – *Table 2: STM32F413xG/H features and peripheral counts* – *Table 12: STM32F413xG/H alternate functions* Added: – *Table 11: FSMC pin definition*